

# R1200F THRU R2000F

## Features

- Low Cost
- Low Leakage
- Low Forward Voltage Drop
- High Current Capability
- High Voltage
- Fast Switching For Higher Efficiency

## Maximum Ratings

- Operating Temperature: -65°C to +150°C
- Storage Temperature: -65°C to +150°C

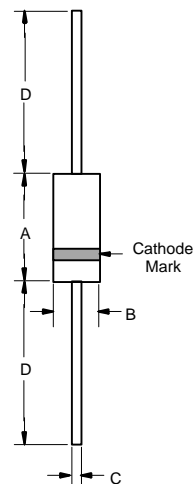
Microsemi Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
R1200	---	1200V	840V	1200V
R1500	---	1500V	1050V	1500V
R1800	---	1800V	1260V	1800V
R2000	---	2000V	1400V	2000V

## Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	500mA	$T_A = 50^\circ\text{C}$
Peak Forward Surge Current	$I_{FSM}$	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage R1200-R1800 R2000	$V_F$	1.6V 2.6V	$I_{FM} = 0.5A$ ; $T_A = 50^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	$I_R$	5.0μA 50μA	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$
Typical Junction Capacitance	$C_J$	30pF	Measured at 1.0MHz, $V_R=4.0V$
Maximum Reverse Recovery Time	$T_{rr}$	500nS	

## 500 Milliamp High Voltage Fast Recovery Silicon Rectifier 1200 to 2000 Volts

### DO-41



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.166	.205	4.10	5.20	
B	.080	.107	2.00	2.70	
C	.028	.034	.70	.90	
D	1.000	---	25.40	---	

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